

# C3D03065E

650 V, 3 A Silicon Carbide Schottky Diode

## Features

- 650-Volt Schottky rectifier
- Zero reverse recovery current
- Zero forward recovery voltage
- High-frequency operation
- Temperature-independent switching behavior
- Extremely fast switching
- Positive temperature coefficient on  $V_f$



TO-252-2



Package Types: TO-252-2

PN: C3D03065

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## Applications

- Switch mode power supplies (SMPS)
- Boost diodes in PFC or DC/DC stages
- Free wheeling diodes in inverter stages
- AC/DC converters

## Benefits

- Replace bipolar with unipolar rectifiers
- Essentially no switching losses
- Higher efficiency
- Reduction of heat sink requirements
- Parallel devices without thermal runaway

## Maximum Ratings ( $T_c = 25\text{ }^\circ\text{C}$ Unless Otherwise Specified)

Parameter	Symbol	Value	Unit	Test Conditions	Note
Repetitive Peak Reverse Voltage	$V_{RRM}$	650	V		
Surge Peak Reverse Voltage	$V_{RSM}$	650			
DC Blocking Voltage	$V_{DC}$	650			
Continuous Forward Current	$I_F$	11	A	$T_c = 25\text{ }^\circ\text{C}$	Fig. 3
		5		$T_c = 135\text{ }^\circ\text{C}$	
		3		$T_c = 158\text{ }^\circ\text{C}$	
Repetitive Peak Forward Surge Current	$I_{FRM}$	18	A	$T_c = 25\text{ }^\circ\text{C}$ , $t_p = 10\text{ ms}$ , Half Sine Wave $D=0.3$	
		13.5		$T_c = 110\text{ }^\circ\text{C}$ , $t_p = 10\text{ ms}$ , Half Sine Wave $D=0.3$	
Non-Repetitive Peak Forward Surge Current	$I_{FSM}$	26	A	$T_c = 25\text{ }^\circ\text{C}$ , $t_p = 10\text{ ms}$ , Half Sine Wave $D=0.3$	
		23		$T_c = 110\text{ }^\circ\text{C}$ , $t_p = 10\text{ ms}$ , Half Sine Wave $D=0.3$	
Non-Repetitive Peak Forward Surge Current	$I_{FSM}$	100	A	$T_c = 25\text{ }^\circ\text{C}$ , $t_p = 10\text{ }\mu\text{s}$ , Pulse	
Power Dissipation	$P_{tot}$	47	W	$T_c = 25\text{ }^\circ\text{C}$	Fig. 4
		20		$T_c = 110\text{ }^\circ\text{C}$	
Diode $dV/dt$ Ruggedness	$dV/dt$	200	V/ns	$V_R = 0\text{--}650\text{ V}$	
Operating Junction and Storage Temperature	$T_J, T_{stg}$	-55 to +175	$^\circ\text{C}$		



## Electrical Characteristics

Parameter	Symbol	Typ.	Max.	Unit	Test Conditions	Note
Forward Voltage	$V_F$	1.5	1.7	V	$I_F = 3 \text{ A}, T_J = 25 \text{ }^\circ\text{C}$	Fig. 1
		1.8	2.4		$I_F = 3 \text{ A}, T_J = 175 \text{ }^\circ\text{C}$	
Reverse Current	$I_R$	5	24	$\mu\text{A}$	$V_R = 650 \text{ V}, T_J = 25 \text{ }^\circ\text{C}$	Fig. 2
		9.5	96		$V_R = 650 \text{ V}, T_J = 175 \text{ }^\circ\text{C}$	
Total Capacitive Charge	$Q_C$	7.6		nC	$V_R = 400 \text{ V}, I_F = 3 \text{ A}$ $di/dt = 500 \text{ A}/\mu\text{S}$ $T_J = 25 \text{ }^\circ\text{C}$	Fig. 5
Total Capacitance	C	166		pF	$V_R = 0 \text{ V}, T_J = 25 \text{ }^\circ\text{C}, f = 1 \text{ MHz}$	Fig. 6
		14			$V_R = 200 \text{ V}, T_J = 25 \text{ }^\circ\text{C}, f = 1 \text{ MHz}$	
		11			$V_R = 400 \text{ V}, T_J = 25 \text{ }^\circ\text{C}, f = 1 \text{ MHz}$	
Capacitance Stored Energy	$E_C$	1.1		$\mu\text{J}$	$V_R = 400 \text{ V}$	Fig. 7

Note: This is a majority carrier diode, so there is no reverse recovery charge.

## Thermal Characteristics

Parameter	Symbol	Typ.	Unit	Note
Thermal Resistance from Junction to Case	$R_{\theta JC}$	3.2	$^\circ\text{C}/\text{W}$	Fig. 8

## Typical Performance

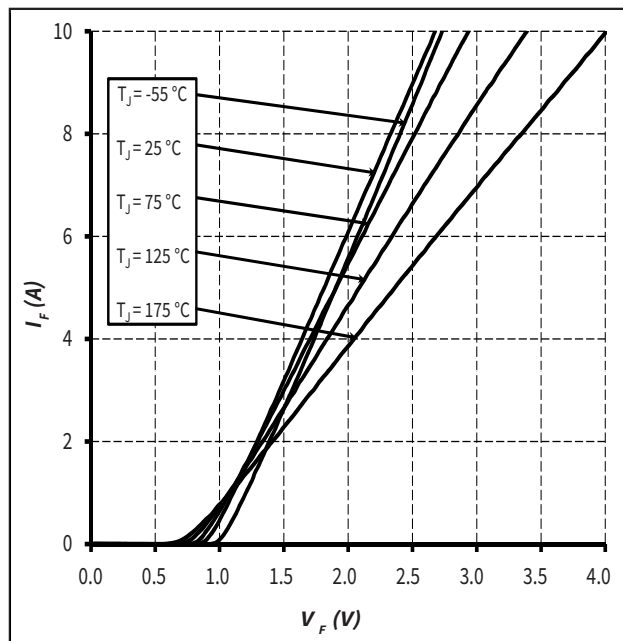


Figure 1. Forward Characteristics

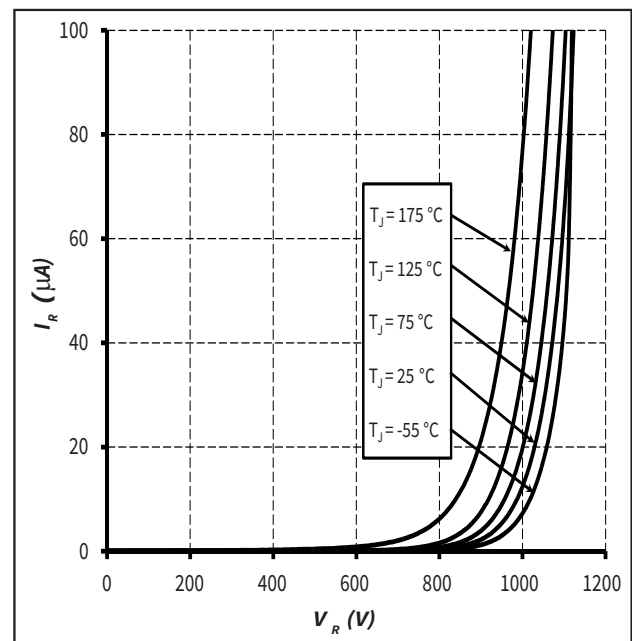


Figure 2. Reverse Characteristics



Typical Performance

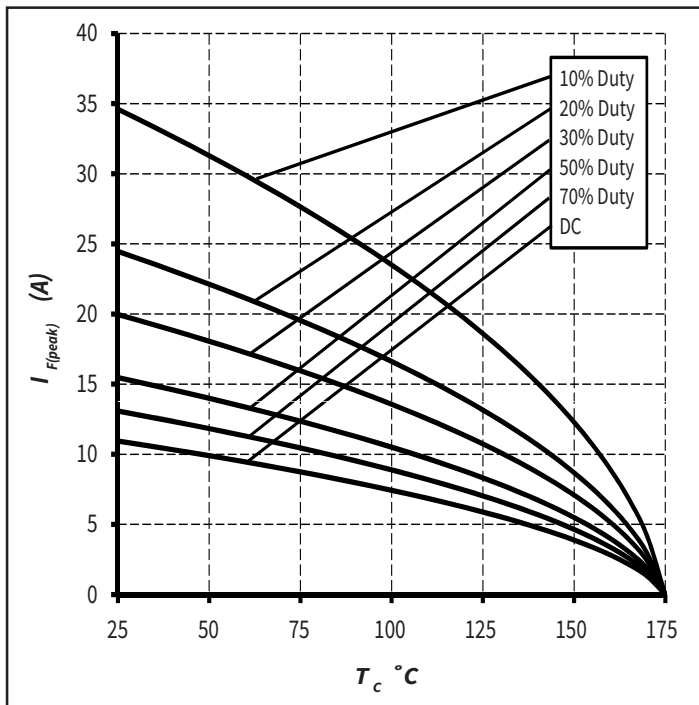


Figure 3. Current Derating

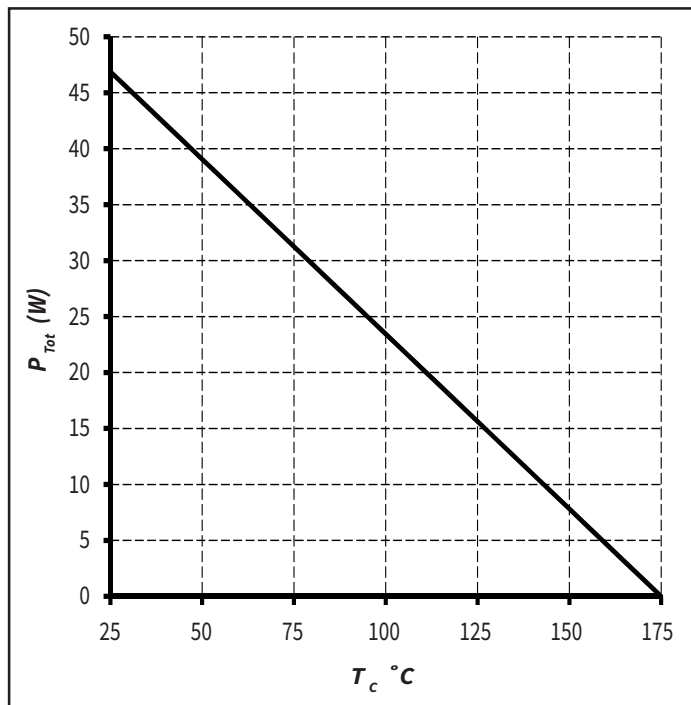


Figure 4. Power Derating

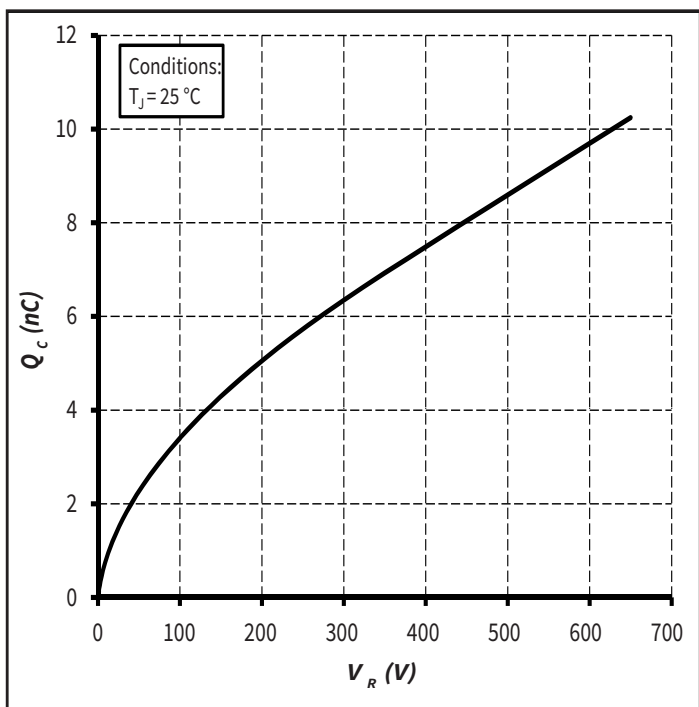


Figure 5. Total Capacitance Charge vs. Reverse Voltage

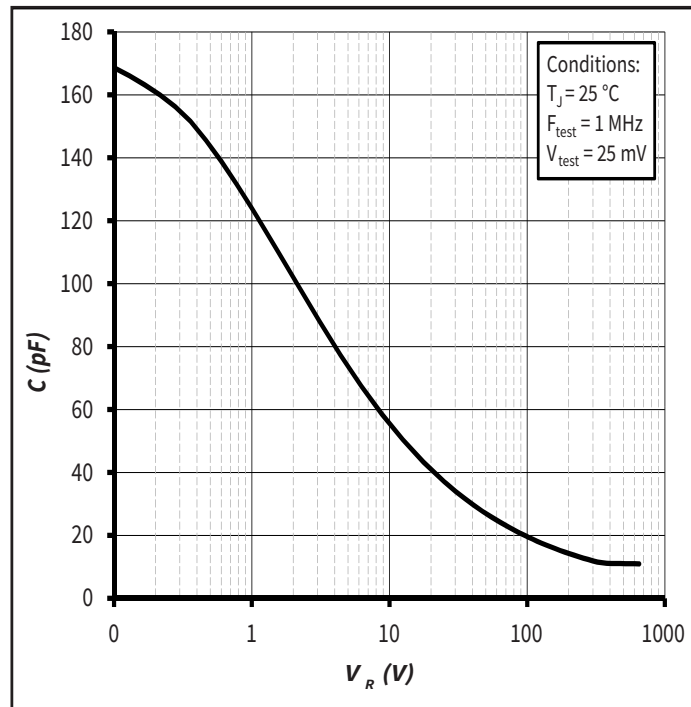


Figure 6. Capacitance vs. Reverse Voltage



### Typical Performance

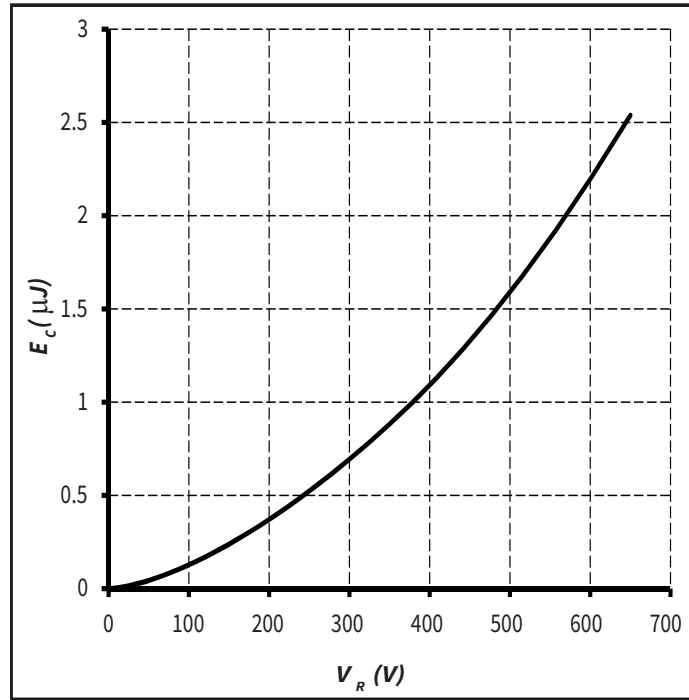


Figure 7. Capacitance Stored Energy

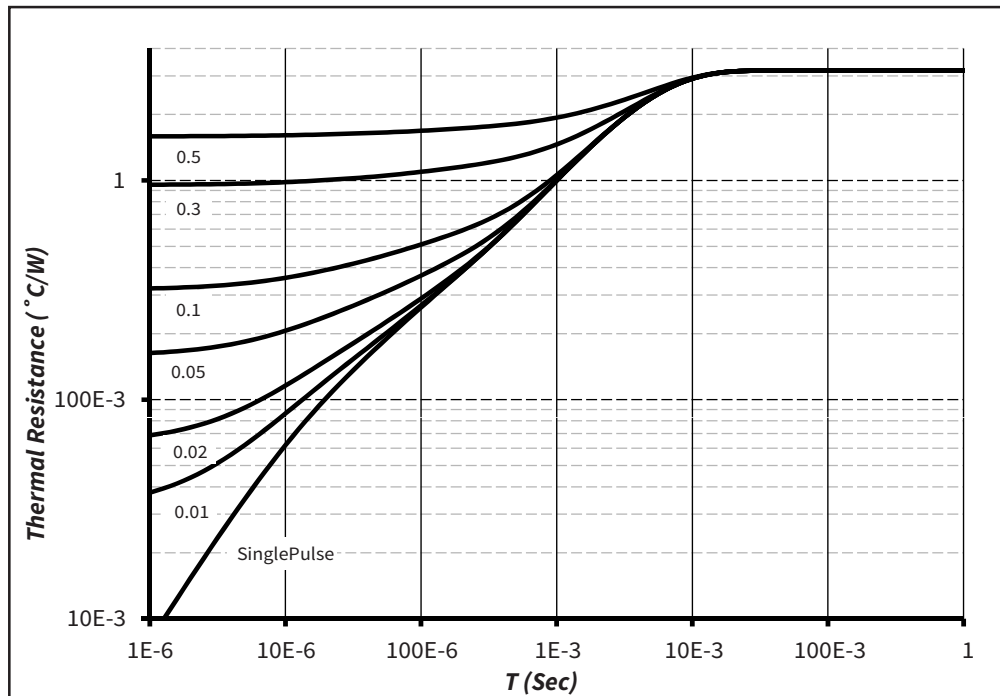
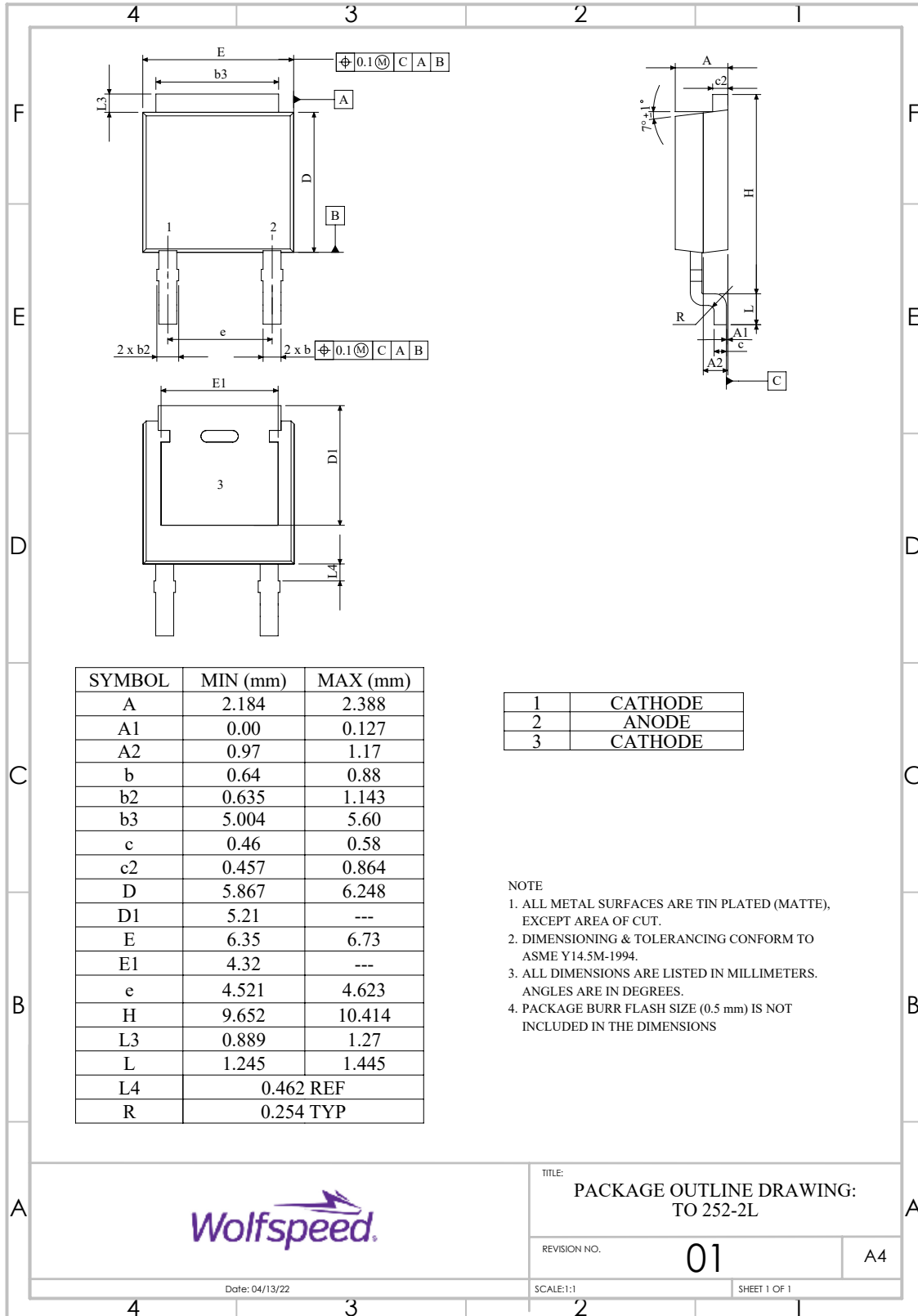


Figure 8. Transient Thermal Impedance



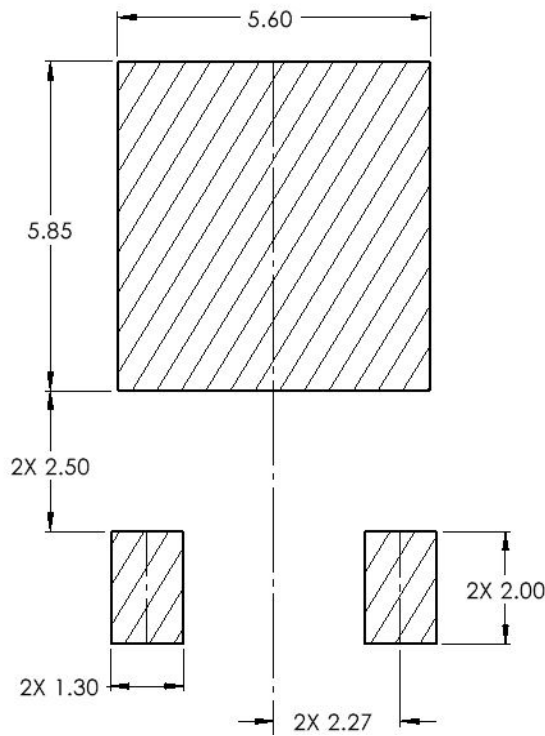
### Package Dimensions

Package: TO-252-2



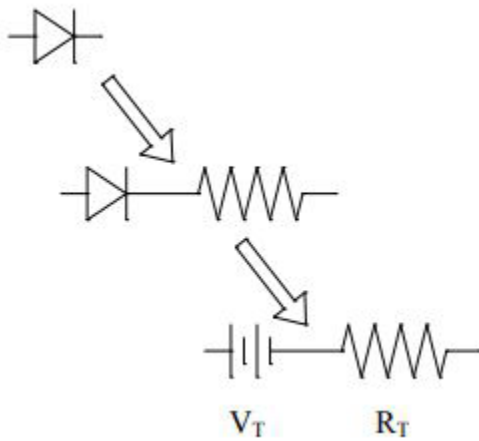


### Recommended Solder Pad Layout



Part Number	Package	Marking
C3D03065E	TO-252-2	C3D03065

### Diode Model



$$V_{f_T} = V_T + I_f * R_T$$

$$V_T = 0.96 + (T_J * -1.1 * 10^{-3})$$

$$R_T = 0.145 + (T_J * 9.5 * 10^{-4})$$

Note:  $T_J$  = Diode Junction Temperature In Degrees Celsius, valid from 25°C to 175°C



## Revision History

Current Revision	Date of Release	Description of Changes
5	September-2023	Updated Wolfspeed branding, package drawing, and solder pad layout, Removed AEC-Q101 banner
6	October-2023	Corrected solder pad layout and diode model



## Notes & Disclaimer

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